

Intermediate Band Solar Cells and Materials Characterization Laboratory -Copy out of control-

According with the characteristics of our equipments and the experience we have, IB-LAB has defined the following requirements of samples to be measured at our installations.

Equipment / Technique	Size	Thickness	Type of materials	Metallization	Range of measurement
Cryostat	<1cm Ø	<5mm	2 terminal Semiconductor Devices	YES	6К-298К
Photoreflectan ce	<0.5cmx0.5cm	<10mm	Semiconductor	NO	400nm-2500nm
Quantum Efficiency	<4cmx4cm	<5mm	2 terminal Semiconductor Devices	YES (grid)	400nm-1700nm
I-V	<1cmx1cm	<5mm	2 terminal Semiconductor Devices	YES	100nA-1A
Flash	<1cmx1cm	<5mm	2 terminal Semiconductor Devices	YES	1uA-6A 10ºC-50ºC
FTIR	>1cmx1cm	<5mm	Semiconductor	NO	800nm-20000nm
DLTS	<1cmØ	<5mm	2 terminal Semiconductor Devices	YES	77K-330K
PL	> 0.5cmx0.5cm	<5mm	Semiconductor	NO	300nm-2000nm
EL	< 0.5cmx0.5cm	<5mm	2 terminal Semiconductor Devices	YES	300nm-2000nm
PROFILER	< 10 cm Ø	< 30 mm	Non viscous material	-	1 Å-1.2 μm
PLASMA ASHER	< 3 inches	< 1 inch	Any type of semiconductor but back side can't be viscous	-	Up to 200ºC

ISSUES' CONTROL						
	Elaborated	Reviewed and Authorized	Cancelled			
Name	Irene Artacho	Prof. Antonio Martí				
Position	Researcher	Technical Director				
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